

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

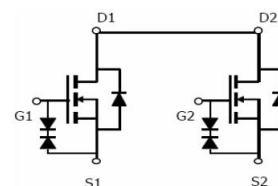
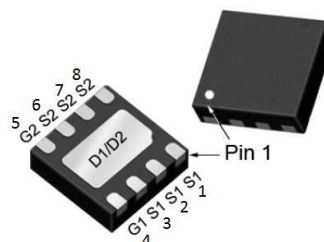


BVDSS	RDSON	ID
20V	4.4mΩ	50A

DFN3030-8L Pin Configurations

FEATURE

- TrenchFET Power MOSFET
- Excellent $R_{DS(on)}$
- Low Gate Charge
- High Power and Current Handling Capability
- Surface Mount Package
- ESD Rating: 2000V HBM



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	50	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	31	A
I_{DM}	Pulsed Drain Current ²	100	A
EAS	Single Pulse Avalanche Energy ³	135	mJ
I_{AS}	Avalanche Current	52	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	---	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	38	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	---	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	---	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=4.5V$, $I_D=8A$	---	4.4	5.2	$m\Omega$
		$V_{GS}=2.5V$, $I_D=6A$	---	5.3	6	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	0.5	0.6	1	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=20V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=20V$, $V_{GS}=0V$, $T_J=100^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V$, $V_{DS}=0V$	---	---	± 7	μA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=4A$	---	10	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	---	---	Ω
Q_g	Total Gate Charge	$V_{DS}=10V$, $V_{GS}=4.5V$, $I_D=6A$	---	36	---	nC
Q_{gs}	Gate-Source Charge		---	3.2	---	
Q_{gd}	Gate-Drain Charge		---	13	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=10V, I_D=6A$, $R_G=3\Omega$, $V_{GS}=4.5V$	---	8.2	---	ns
T_r	Rise Time		---	35	---	
$T_{d(off)}$	Turn-Off Delay Time		---	372	---	
T_f	Fall Time		---	213	---	
C_{iss}	Input Capacitance	$V_{DS}=10V$, $V_{GS}=0V$, $f=1KHz$	---	2610	---	pF
C_{oss}	Output Capacitance		---	345	---	
C_{rss}	Reverse Transfer Capacitance		---	322	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	50	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1.5A$, $T_J=25^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$I_F=5A$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	---	---	nS
Q_{rr}	Reverse Recovery Charge		---	---	---	nC

Notes :

- 1.Repetitive rating: Pluse width limited by maximum junction temperature
- 2.Surface Mounted on FR4 board, $t \leq 10$ sec.
- 3.. EAS condition : $T_J=25^\circ\text{C}$, $V_{DD}=40V$, $V_G=10V$, $L=0.1mH$, $R_g=25\Omega$, $I_{AS}=52A$
- 4.Pulse test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.Guaranteed by design, not subject to production.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTIC

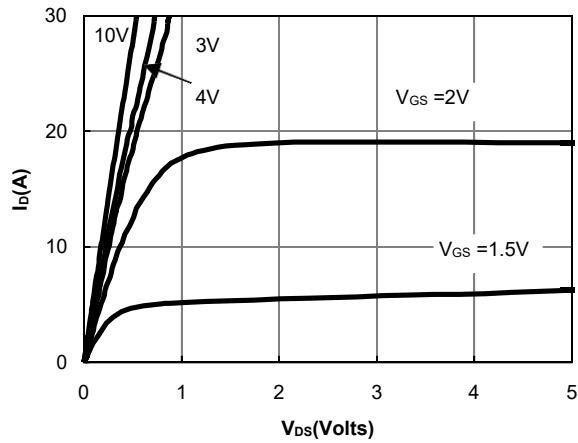


Figure 1: On-Regions Characteristic CS

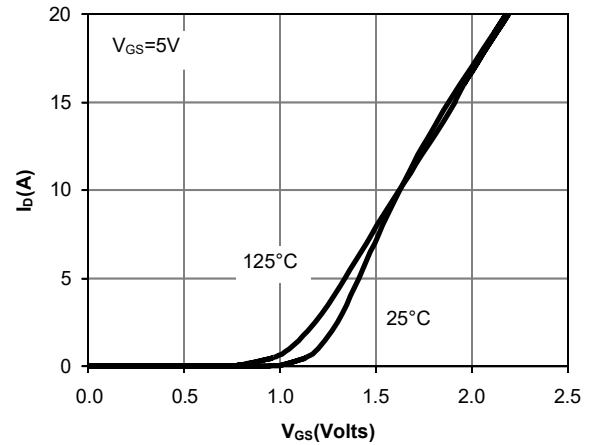


Figure 2: Transfer Characteristics

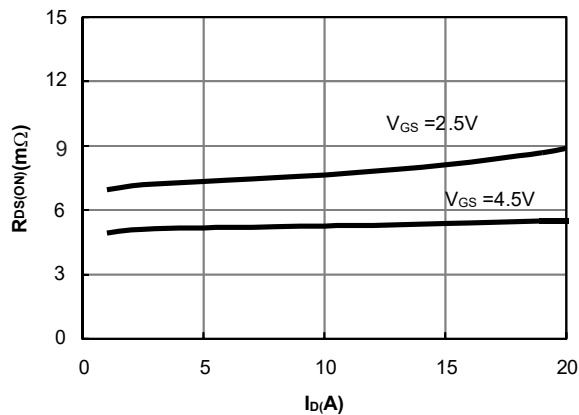


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

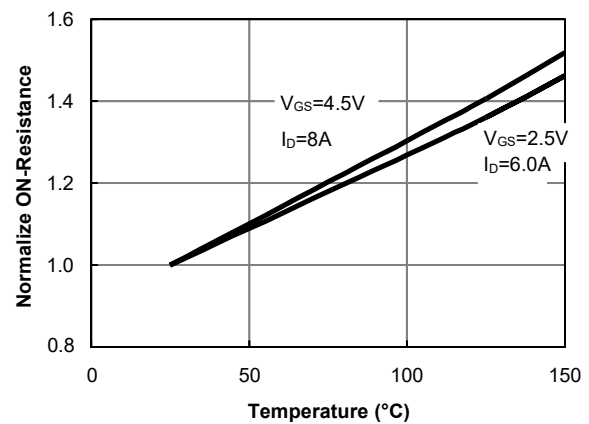


Figure 4: On-Resistance vs. Junction Temperature

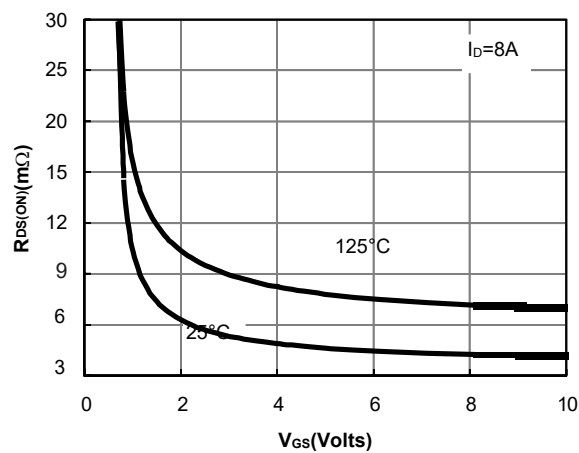


Figure 5: On-Resistance vs. Gate-Source Voltage

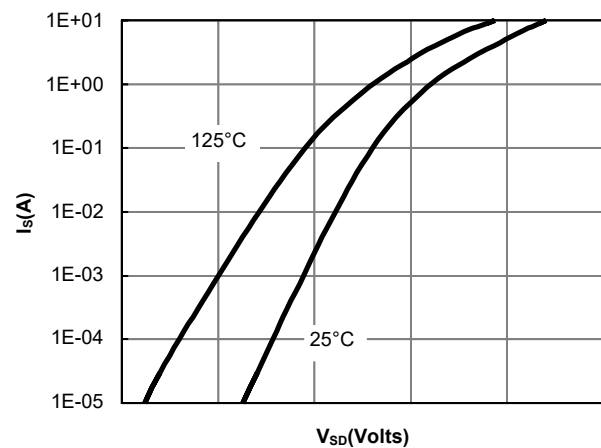


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTIC

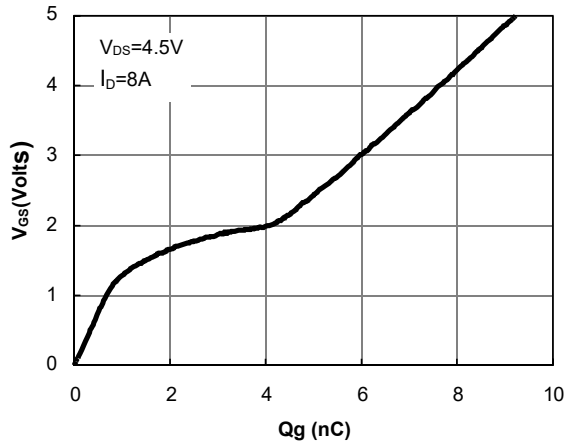


Figure 7: Gate-Charge Characteristics

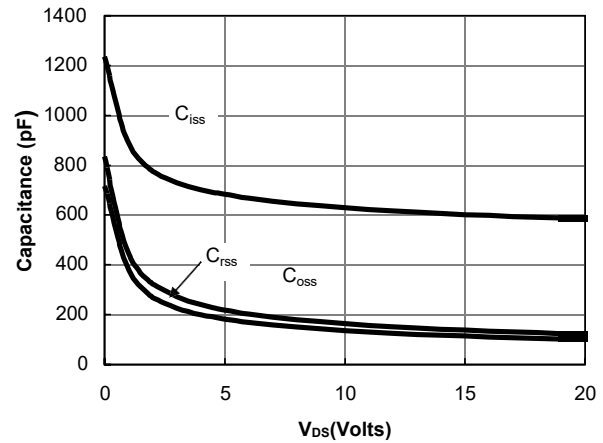


Figure 8: Capacitance Characteristics

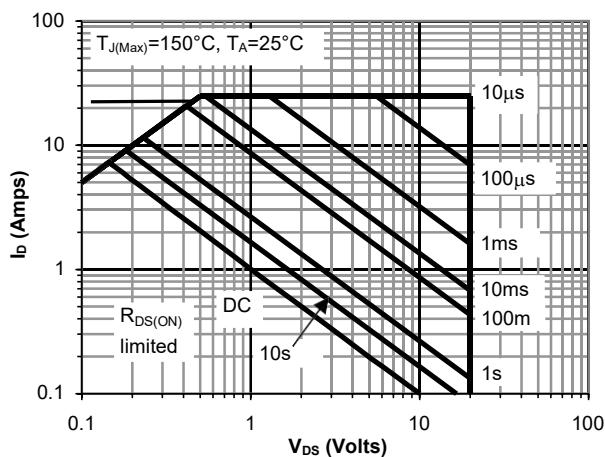


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

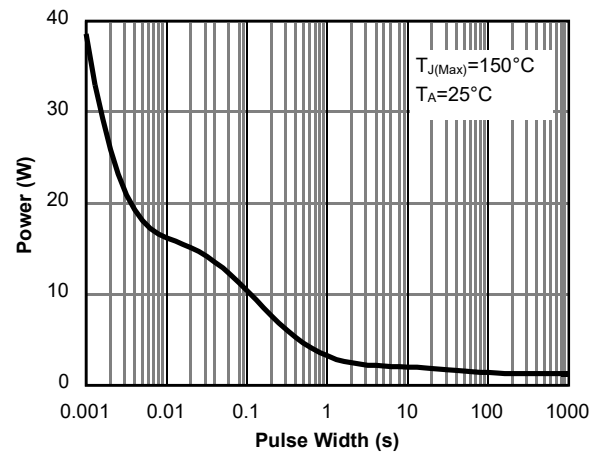


Figure 10: Single Pulse Power Rating Junction-to-Ambient

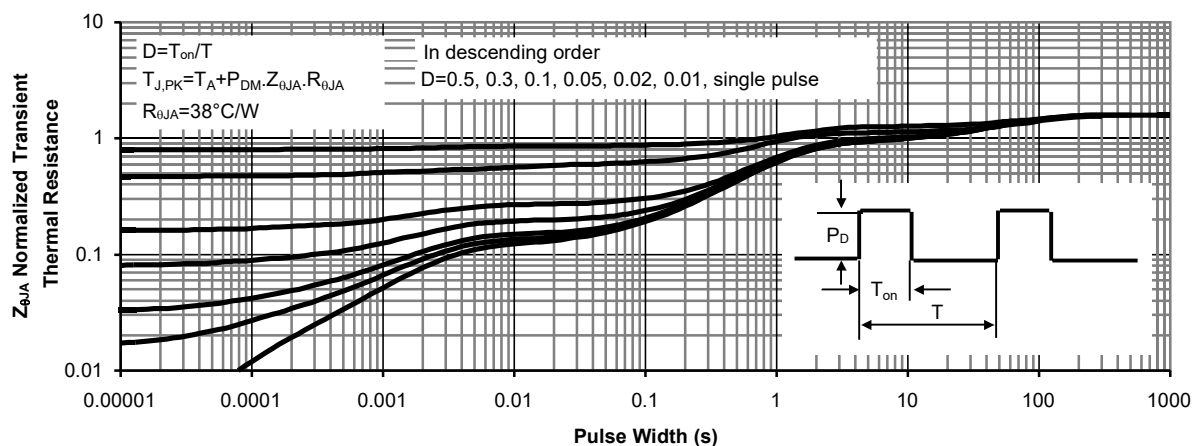
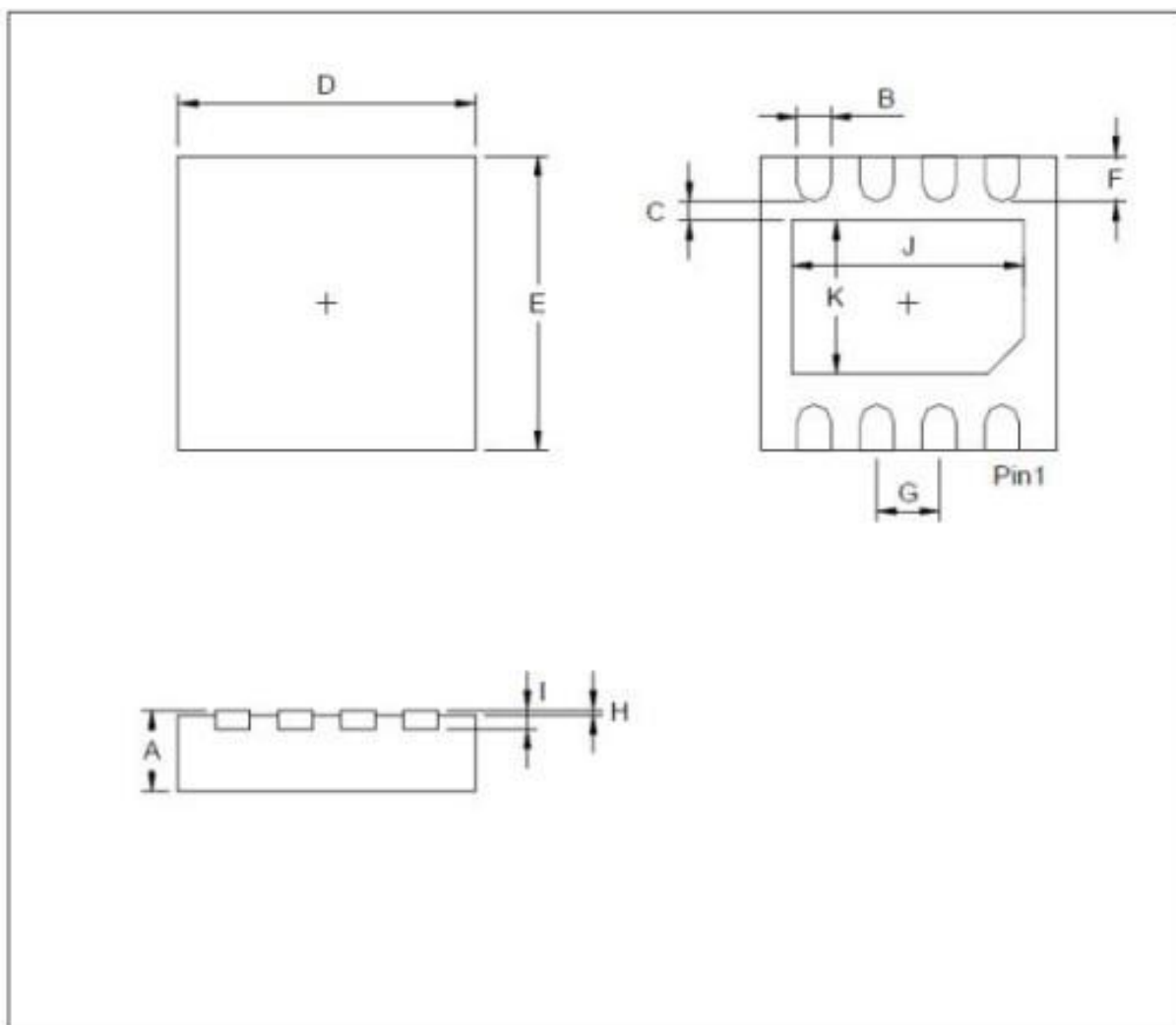


Figure 11: Normalized Maximum Transient Thermal Impedance

DFN3030-8L Package Outline Data



Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	0.7		0.8	I		0.203	
B	0.25		0.35	J	2.2		2.4
C	0.2			K	1.4		1.6
D	2.924		3.076				
E	2.924		3.076				
F	0.324		0.476				
G		0.65					
H	0		0.05				